





Addressing MEMS development challenges Lab-in-Fab approach to accelerate time to volume

#### Andreja Erbes

Director, Technology Scouting and R&D Partnerships

STMicroelectronics

# What is the traditional development cycle of state-of-the-art MEMS products?

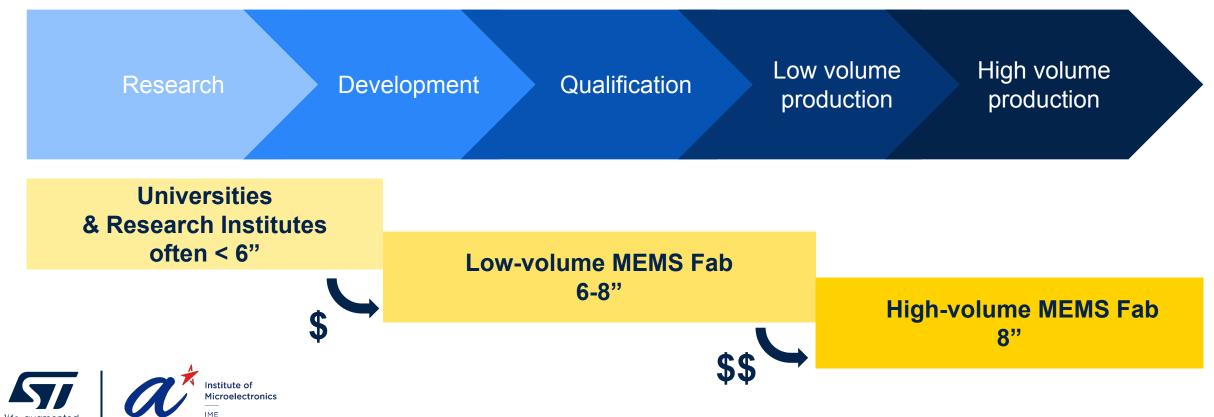
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## "MEMS development 101"

"Classical" development cycle Working with multiple players slows down time-to-volume





#### Can we do better?





## World's first Lab-in-Fab for Piezoelectric MEMS

#### ST Techno Park in Ang Mo Kio (Singapore)







## Lab-in-Fab: accelerating time to volume

Lab-in-Fab model: all under one "roof" Combining all phases in the same place





#### Lab-in-Fab



## Lab-in-Fab

#### Your research and industrialization partner

#### **Our mission**

Become the **global leader** in **microsystems research** and **industrialization**, **accelerating** the commercialization of **leading-edge products** 

#### **Our vision**

**Support customers** in their journey to the **industrialization** of innovative products using advance **piezoelectric** materials, **sensors & actuators** technology platforms

#### How?

By combining **world-class R&D personnel**, key semiconductor equipment and access to the complete **IME & ST development ecosystem** 

# Leading-edge competence & access to the global ecosystem

#### Rapid product development





## Institute of Microelectronics (IME)



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## IME – key expertise

**Combining deep expertise with cutting-edge facilities to conduct** world-class microelectronics research 8" SiC **R&D** line 8900 m<sup>2</sup> of cleanroom 8" Sensor space Class 1 to 10,000 systems 8",12" Photonic systems 6" 8" piezoelectric mmWave specialty at Lab-in-Fab RF GaN 12" Advanced packaging

## We are creators and makers of technology



## ST's global ecosystem

9,500+ people working in R&D and product design

Advanced R&D centers around the globe

A unique portfolio of specialized technologies

## Cooperations is a core fundamental of ST's DNA



14 manufacturing sites

- 7 Front-End sites
- 7 Back-End sites

Offering quality, flexibility, and supply security

More than **30 years** of expertise in advanced semiconductors

More than **20 years** in MEMS

Supporting customers in advanced R&D

## ST Singapore campus

#### Ang Mo Kio



- 1<sup>st</sup> semiconductor front-end plant in Singapore (1984)
- > 51,200 m2 combined cleanroom
- 6" and 8" production areas
- ~ 4,500 employees

#### Large mix of technologies

MEMS & microfluidics, Bipolar, power MOSFET, BCD & advanced BCD, EEPROM, smartcard, CMOS logic & BiCMOS, SiC diode & MOSFET



#### two physical locations = one functional FAB

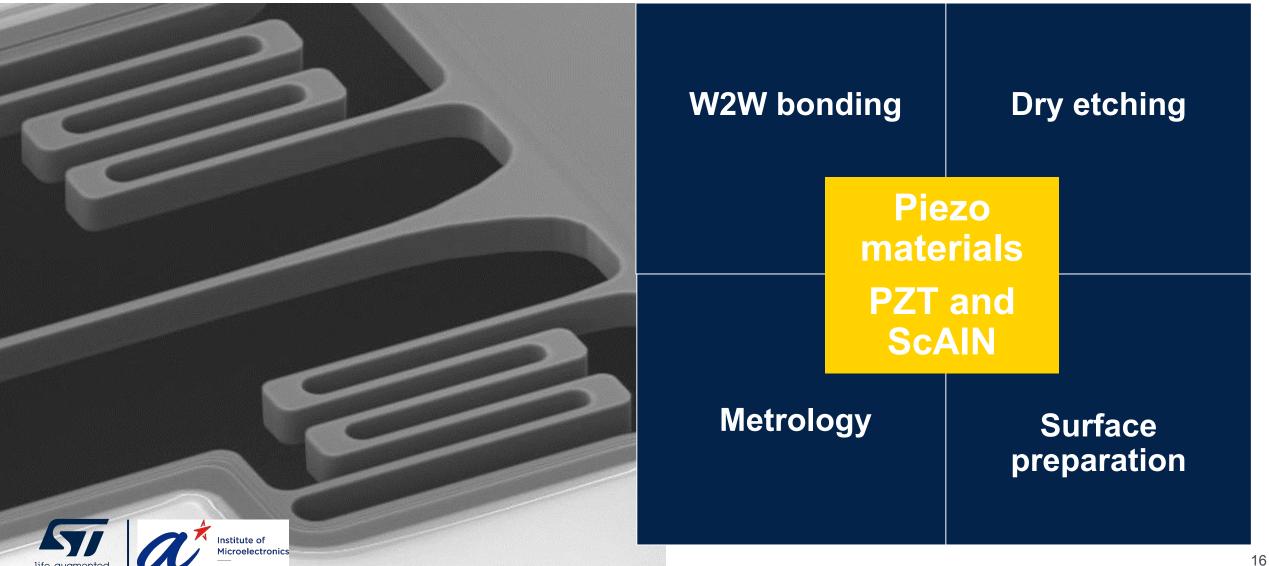


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## Technology platforms



## Key process modules



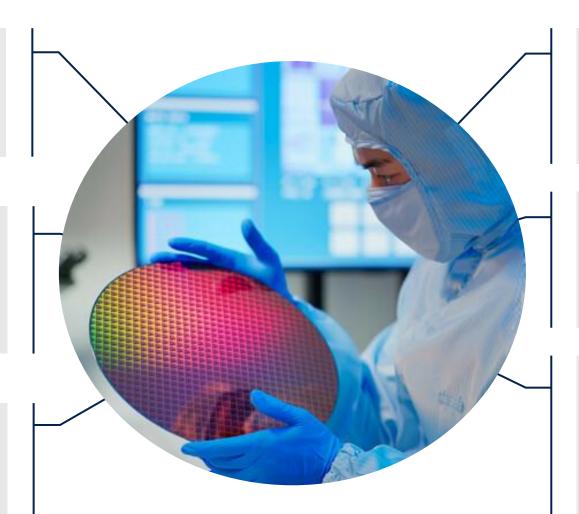
## Lab-in-Fab capabilities

Wet and other etchings: silicon oxide, quartz-glass, polymer, and sacrificial layer removal

Piezo, metal, and protective layer depositions: AIN, ScAIN, PZT, AI, TiW, AICu, Ti, AIO, Pt, SiN, ...

**Dry etching:** silicon, silicon oxide, metal, piezo, photoresist stripping





Metrology: defectivity, ellipsometry, stress, SEM/EDX, metal sheet res, topography, infrared

Wafer-to-wafer bonding: metallic, fusion, organic, temporary bonding

**Lithography:** MEMS stepper with resolution of 0.4 µm, double side alignment accuracy of +/- 0.1 µm

## Lab-in-Fab 8" tool-set in details (1/2)

#### Photolithography



- Steppers and mask aligner (1x)
- Front to back alignment
- Up to 0.4 um resolution
- Thick and thin resist
- Screen printing



#### Thin-film



- Oxide and SiN CVD
- AIO and HfO ALD
- Metals and barriers
- Piezo layers
  - PZT, ScAIN
  - ...

#### Etch



- Metallic etch
- Dielectric etch
- Silicon etch
- PZT and ScAIN etch
- XeF2 Si etch

#### Wafer bonding



- Fusion bonding
- Eutectic bonding
- Polymer bonding
- Temporary bonding
- Back grinding and edge trimming

## Lab-in-Fab 8" tool-set in details (2/2)

**Inspection and** 

Engineering

Defectivity scan

Inspection SEM

Defect review

**IR** Inspection

Microscope

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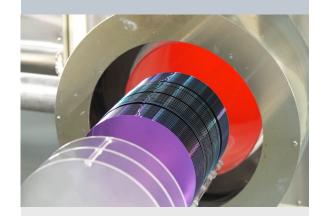
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EDX

#### Others



- CMP
- Anti stiction coating
- Thermal oxidation
- POCL doping
- Dry resist strip
- Descum

#### Wet and Cleaning



- Front and back scrub
- Wet etches, cleanings and polymer removal
- Backside decon.
- Wet resist strip
- Vapor HF release

#### Metrology



- Film thickness
- Film stress
- Resistivity
- Alignment and CD
- XRD
- DBLI

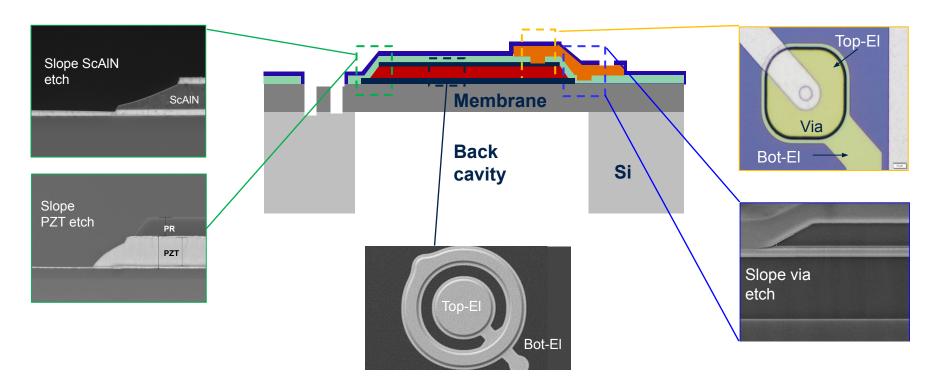


### Example of applications



## Lab-in-Fab MPW service

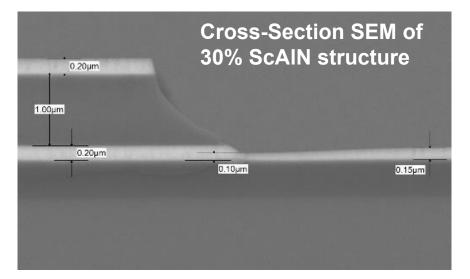
#### **PVD PZT & ScAIN platforms**



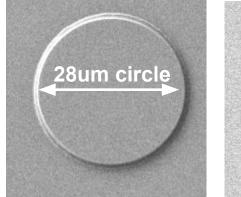
#### **Key applications**

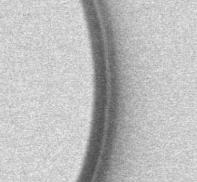
- PMUT
- Microphone, micro speaker
- RF resonators
- Other custom designs compatible with proposed process platforms

## Multilayer ScAIN MEMS

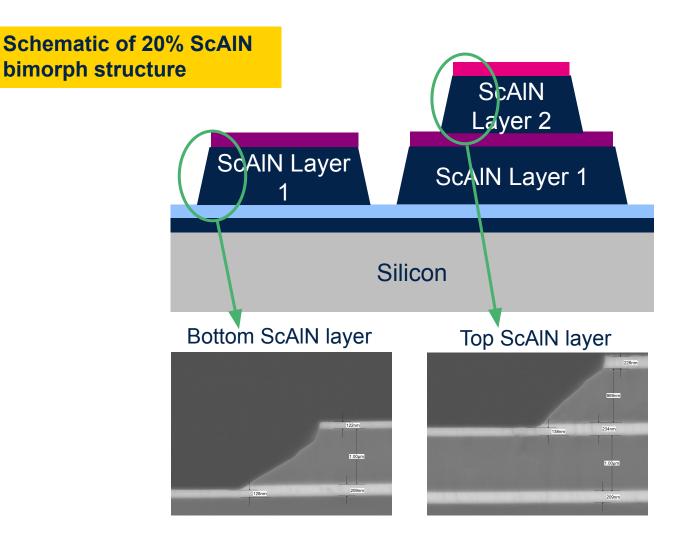


#### **SEM** top views



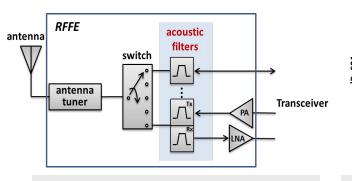






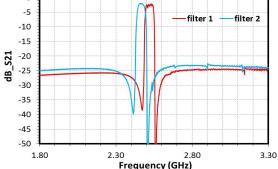
## **RF MEMS platform**

## Acoustic filters for RF front-end systems



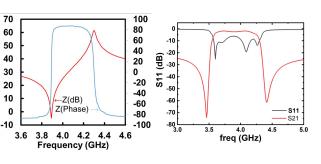
- Addressing RF front end (RFFE) using high performance MEMS technology
- Acoustic filters
- Frequency reference for oscillators

## Lamb wave resonator technology



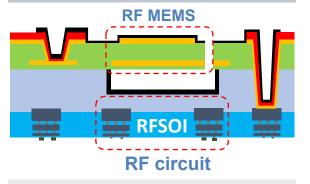
- Lithographic frequency tunability
- Multiple frequencies on one wafer
- Fab cost reduction

## Bulk acoustic wave (BAW) technology



- Various Sc% doping for customized design
- Frequency ranging from 700 MHz to 15 GHz
- High quality factor and high bandwidth filter

## Monolithic integration technology



- Acoustic filter monolithically integrated with CMOS circuits
- Minimize the footprint of RF module
- Parasitic reduction







## Lab-in-Fab engagement model



Phase

**First level assessment** no NDA required

 Assess alignment with Lab-in-Fab technology roadmap, Fab toolset and capability





**In-depth assessment** under NDA

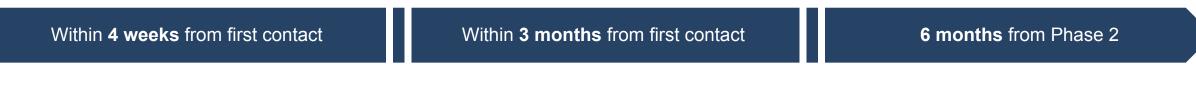
- **Technical**: feasibility of process flow, rough estimate of resources needed, high level schedule
- Business: estimate of development cost, high level IP alignment



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Phase **Contractual agreement SOW or development** agreement, signed

- Covering all technical and business aspects
- Technical activity can start in parallel





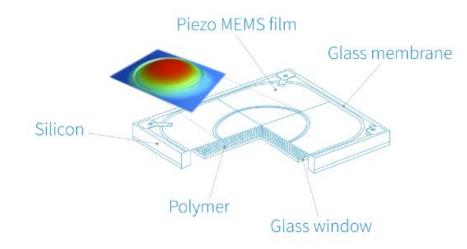
## Examples of third-party collaborations

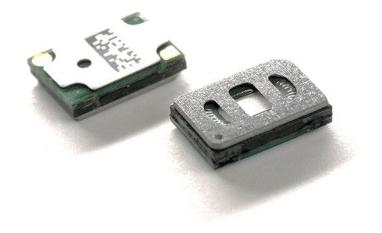














## Lab-in-Fab



#### Want to know more? Contact us at Lab\_in\_Fab\_List@list.st.com

#### **EMEA** and Asia

Tarik SOUIBES: tarik.souibes@st.com Valentina BAIARDO: valentina.baiardo@st.com

**US** Matteo FUSI: matteo.fusi@st.com



## Our technology starts with You



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